

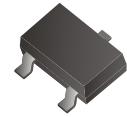
SMD Switching Diode



SMD Diodes Specialist

CDST193-G

RoHS Device

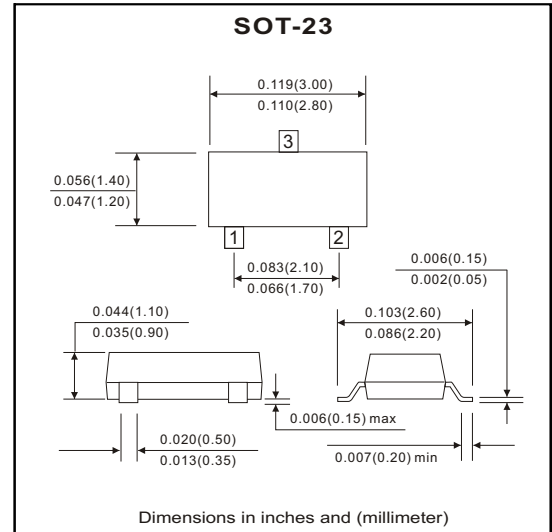


Features

- Low forward voltage: $V_F=0.9V$ (Typ.)
- Fast reverse recovery time: $t_{rr}=1.6nS$ (Typ.)

Polarity: 1. ANODE
2. N.C.
3. CATHODE

Marking: F3



Maximum Ratings (at $T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Non-repetitive peak reverse voltage	V_{RM}	85	V
DC blocking voltage	V_R	80	V
Forward continuous current	I_{FM}	300*	mA
Average rectified output current	I_o	100*	mA
Power dissipation	P_D	150	mW
Junction temperature	T_J	125	$^{\circ}C$
Storage temperature	T_{STG}	-55 ~ +125	$^{\circ}C$

*Unit rating. Total rating=Unit rating \times 1.5

Electrical Characteristics (at $T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Min	Max	Unit
Reverse breakdown voltage	$I_R=100\mu A$	$V_{(BR)R}$	80			V
Forward voltage	$I_F=1mA$	V_{F1}		0.60		V
	$I_F=10mA$	V_{F2}		0.72		V
	$I_F=100mA$	V_{F3}		0.90	1.2	V
Reverse current	$V_R=30V$	I_{R1}			0.1	μA
	$V_R=80V$	I_{R2}			0.5	μA
Capacitance between terminals	$V_R=0V, f=1MHz$	C_T		0.90	3.0	pF
Reverse recovery time	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R$	t_{rr}		1.60	4.0	nS

RATING AND CHARACTERISTIC CURVES (CDST193-G)

Fig.1 Forward Voltage Characteristics

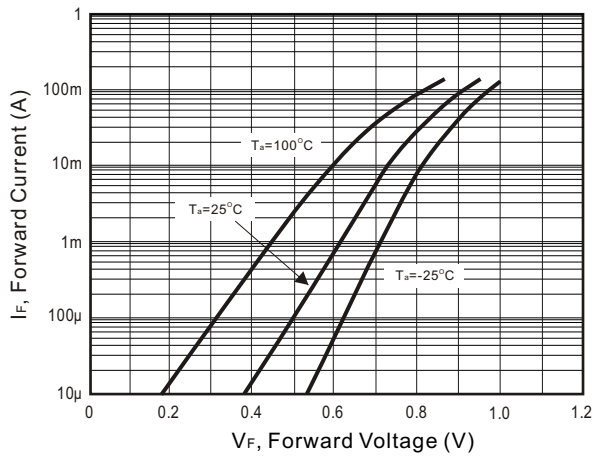


Fig.2 Reverse Characteristics

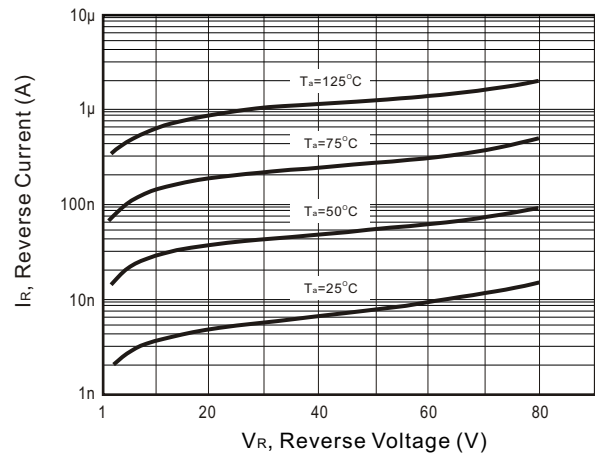


Fig.3 Capacitance Between Terminals

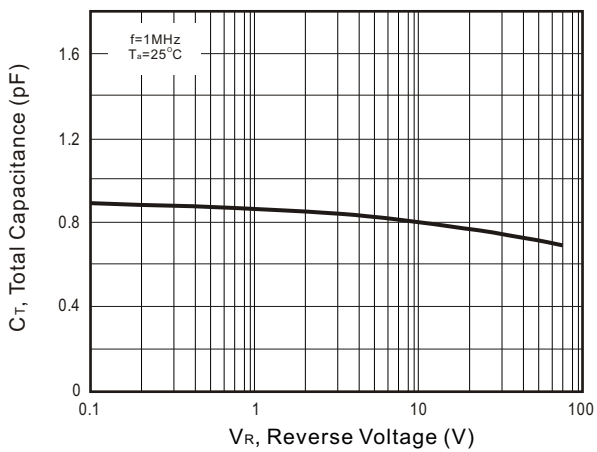


Fig.4 Reverse Recovery Time Characteristics

